

Form 349 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. NOVLP096/NVLS-2902	Application No.: 10/815,560
	Applicant: Wongsenakhum et al. Filing Date March 31, 2004	Group 2823




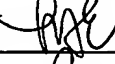
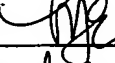
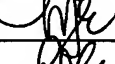
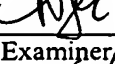
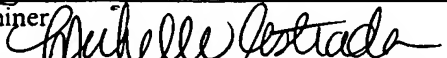
U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
<i>[Signature]</i>	A1	6,635,965	10.21.03	Lee et al.	—	—	
	A2	6,607,976	08/19/03	Chen et al.	—	—	
	A3	6,740,585	05/25/04	Yoon et al.	—	—	
	A4	6,861,356	03/01/05	Matsuse et al.	—	—	
	A5	6,107,200 A	08.2000	Takagi et al.	—	—	
	A6	6,844,258	01.18.05	Fair et al.	—	—	
	A7	6,174,812	01/16/01	Hsiung, et al.	—	—	
	A8	6,566,250	05/20/03	Tu, et al.	—	—	
	A9	6,566,262	05/20/03	Rissman, et al.	—	—	
	A10	6,706,625	03/16/04	Sudijono, et al.	—	—	
	A11	2004/0044127	03.04.04	Okubo et al.	—	—	
	A12	2004/0206267	10.21.04	Sambasivan et al.	—	—	

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
<i>[Signature]</i>	B1	WO01/27147	04/19/01	WIPO			X	

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	U.S. Office Action mailed July 17, 2002, from U.S. Application No. 09/975,074 [Atty Dkt. NOVLP033/NVLS-000498].
	C2	U.S. Office Action mailed February 8, 2005, from U.S. Application No. 10/649,351 [Atty Dkt. NOVLP033X1/NVLS-000498X1].
	C3	U.S. Office Action mailed July 14, 2005, from U.S. Application No. 10/649,351 [Atty Dkt. NOVLP033X1/NVLS-000498X1].
	C4	Presentation by Inventor James Fair: "Chemical Vapor Deposition of Refractory Metal Silicides," 27 Pages, 1983
	C5	Saito et al., "A Novel Copper Interconnection Technology Using Self Aligned Metal Capping Method," IEEE, 3 Pages, 2001
	C6	U.S. Office Action mailed June 22, 2004, from U.S. Application No. 10/435,010 [Atty Dkt. NOVLP058/NVLS-000730].
	C7	U.S. Office Action mailed March 23, 2005, from U.S. Application No. 10/690,492 [Atty Dkt. NOVLP063/NVLS-000615].
Examiner 	Date Considered 12/14/05	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. NOVLP096/NVLS-2902	Application No.: 10/815,560
	Applicant: Wongsenakhum et al.	
	Filing Date March 31, 2004	Group 2823

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>[Signature]</i>	C8	Levy e al., "Deposition of Tungsten Nitride", Novellus Systems, Inc., filed October 20, 2003, Application No. 10/690,492, pages 1-42. [Atty Dkt. NOVLP063/NVLS-000615]
<i>[Signature]</i>	C9	Lee et al., "Method for Reducing Tungsten Film Roughness and Improving Step Coverage", Novellus Systems, Inc., filed August 26, 2003, Application No. 10/649,351, pages 1-40. [NOVLP033X1/NVLS-000498X1]
<i>[Signature]</i>	C10	Fair et al., "Selective Refractory Metal and Nitride Capping", Novellus Systems, Inc., filed November 8, 2004, Appln No. 10/984,126, pages 1-22. [NOVLP058D1/NVLS-000732D1]
Examiner <i>[Signature]</i>	Date Considered <i>12/14/05</i>	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
<i>ME</i>	A1	2002/0177316	11.2002	Miller et al.			
<i>ME</i>	A2	6,962,873	11.2005	Park, Heung L.			

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub- class	Translation	
							Yes	No

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>ME</i>	C1	U.S. Office Action mailed November 8, 2004, from U.S. Application No. 10/984,126 [Atty Dkt. NOVLP058D1/NVLS-000732D1].
<i>ME</i>	C2	Chan et al., "Methods for Growing Low-Resistivity Tungsten Film", Novellus Systems, Inc., filed November 1, 2005, Application No. 11/265,531, pages 1-35. [NOVLP137/NVLS-0003093]
Examiner <i>Michelle Estrada</i>	Date Considered <i>12/22/05</i>	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.